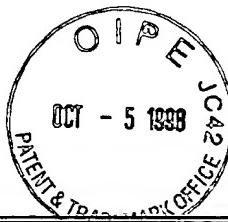


Form PTO-1449 (Modified)
 LIST OF PATENTS AND PUBLICATIONS
 FOR APPLICANT'S INFORMATION
 DISCLOSURE STATEMENT
 Use several sheets if necessary



ATTY. DOCKET NO.
 79329

SERIAL NO.
 09/137,084

APPLICANT
 Stumborg, Michael F. et al.
 FILING DATE
 08/20/98

GROUP
 2811

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
VN	AA	4,502,209	3/5/85	Eizenberg et al.	29	589	-
	AB	4,965,656	10/23/90	Koubuchi et al.	357	71	-
	AC	5,389,575	2/14/95	Chin et al.	437	190	-
	AD	5,489,548	2/6/96	Niskioka et al.	437	60	-
	AE	5,547,901	8/20/96	Kim et al.	437	187	-
	AF	5,552,341	9/3/96	Lee	437	192	-
	AG	5,554,254	9/10/96	Huang et al.	156	625.1	-
	AH	5,624,874	4/29/97	Lim et al.	438	653	-
	AI	5,637,533	6/10/97	Choi	437	643	-
	AJ	5,668,054	9/16/97	Sun et al.	438	653	-
VN	AK	5,670,420	9/23/97	Choi	437	189	-

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO

RECEIVED

OCT 13 1998

GROUP 2100

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

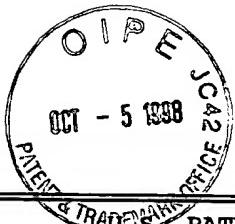
EXAMINER HUNG K. VU

DATE CONSIDERED
 09/21/08

EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

(Information Disclosure Statement - Section 9 PTO-1449 (Modified) [6-1] page 01 of 03)

• Form PTO-1449 (Modified)
LIST OF PATENTS AND PUBLICATIONS
FOR APPLICANT'S INFORMATION
DISCLOSURE STATEMENT
Use several sheets if necessary



ATTY. NO. REC'D. NO.
79329

SERIAL NO.
09/137,084

APPLICANT
Stumborg, Michael F. et al.
FILING DATE GROUP
08/20/98 2812

REFERENCE DESIGNATION

PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER HUNG K VV

DATE CONSIDERED

09/21/00

04/21/60
EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

(Information Disclosure Statement - Section 9 PTO-1449 (Modified) [6-1] page 02 of 03)

Form PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent & Trademark Office	Atty. Docket No. N.C. 79329	Serial No. 09/137,084
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant Stumborg, et al.	
		Filing Date August 20, 1998	Group 2811

IP
FEB 09 1999
U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
Vu	4,291,327	9/22/81	Tsang	357	52	-
	4,550,331	10/29/85	Milano	357	24	
	4,692,993	9/15/87	Clark et al.	437	53	
	4,847,666	7/11/89	Heremans et al.	357	16	
	5,124,762	6/23/92	Childs et al.	357	16	
	5,435,264	7/25/95	Santiago et al.	117	92	
	5,391,517	2/21/95	Gelatos et al.	437	190	
Vu	5,773,359	6/30/98	Mitchell et al.	438	614	-

FOREIGN PATENT DOCUMENTS

	Document	Date	Country	Class	Sub-class	Translation Yes/No
Vu	2-266569	10/31/90	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Vu	S.M. Sze, "Semiconductor Devices Physics and Technology", 1985, pp. 208-210.
Vu	Truscott, et al., "MBE growth of BaF ₂ /(Ga,In)(As,Sb) Structures", Journal of Crystal Growth, Vol. 81 (1987), pp. 552-556.
Vu	Clemens, et al., "Growth of BaF ₂ and of BaF ₂ /SrF ₂ layers on (001) oriented GaAs", J. Appl. Phys., Vol. 66, No. 4, 15 Aug. 1989, pp. 1680-1685.
Vu	Hung, et al., "Epitaxial growth of alkaline earth fluoride films on HF-treated Si and (NH ₄) ₂ S _x -treated GaAs without <i>in situ</i> cleaning", Appl. Phys. Lett., Vol. 60, No. 2, 13 Jan. 1992, pp. 201-203.

EXAMINER HUNG K. VU RE	DATE CONSIDERED 09/21/00
--------------------------------------	-----------------------------

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

RECEIVED
FEB 10 1999
GROUP 2100

Form PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent & Trademark Office	Atty. Docket No. N.C. 79329	Serial No. 09/137,084
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant Stumborg, et al.	
		Filing Date August 20, 1998	Group 2811

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
V		5,690,737	11/25/95	Santiago et al.	117	92	-
N		5,695,810	12/9/97	Dubin et al.	427	96	-
V		5,824,599	10/20/98	Schacham-Diamond, et al.	437	230	-

FOREIGN PATENT DOCUMENTS

		Document	Date	Country	Class	Sub-class	Translation Yes/No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

V	Chaudhari, et al., "Calcium Fluoride thin films on GaAs (100) for possible metal-insulator-semiconductor applications", Appl. Phys. lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.
	Colbow, et al., "Photoemission study of the formation of SrF ₂ /GaAs(100) and BaF ₂ /GaAs(100) interfaces", Physical Review B, Vol. 49, No. 3, 15 Jan. 1994, pp. 1750-1756.
	Chu, et al., "The Role of Barium in the Heteroepitaxial Growth of Insulator and Semiconductors on Silicon", Mat. Res. Symp. Proc., Vol. 334, 1994, pp. 501-506.
	Stumborg, et al., "Determination of growth mechanisms of MBE grown BaF ₂ on Si(100) by target angle dependence of RBS yields", Nucl. Instr. and Methods in Physics Res. B, Vol. 95, 1995, pp. 319-322.
	Stumborg, et al., "Growth and interfacial chemistry of insulating (100) barium fluoride on gallium arsenide", J. Appl. Phys., Vol. 77, No. 6, 15 March 1995, pp. 2739-2744.
	Stumborg, et al., "Surface chemical state populations in the molecular beam epitaxy deposition of BaF ₂ on GaAs by x-ray photoelectron spectroscopy and heavy-ion backscattering spectroscopy", J. Vac. Sci. Technol., Vol. 14, No. 1, Jan./Feb. 1996, pp. 69-79.
V	Chu, et al., "Heteroepitaxial deposition of Group IIa fluorides on gallium arsenide", Mat. Sci. and Eng. B, Vol. B47, 1997, pp. 224-234.

EXAMINER	DATE CONSIDERED	RECEIVED
HUNG K. JV	09/21/00	FEB 10 1999 GROUP 2 100

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

Form PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent & Trademark Office	Atty. Docket No. 82149	Serial No. 09/137,084 not yet assigned
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant Stumborg, et al.	SEP 22 1999 PATENT & TRADEMARK OFFICE 2811
		Filing Date 08/20/98 Concurrently	

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
✓	4,291,327	9/22/81	Tsang	357	52	—
✓	4,550,331	10/29/85	Milano	357	24	—
✓	4,692,993	9/15/87	Clark et al.	437	53	—
✓	4,847,666	7/11/89	Heremans et al.	357	16	—
✓	5,124,762	6/23/92	Childs et al.	357	16	—
✓	5,435,264	7/25/95	Santiago et al.	117	92	—
✓	5,391,517	2/21/95	Gelatos et al.	437	190	—
✓	5,773,359	6/30/98	Mitchell et al.	438	614	—

FOREIGN PATENT DOCUMENTS

	Document	Date	Country	Class	Sub-class	Translation Yes/No
✓	2-266569	10/31/90	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	S.M. Sze, "Semiconductor Devices Physics and Technology", 1985, pp. 208-210.
✓	Truscott, et al., "MBE growth of BaF ₂ /(Ga,In)(As,Sb) Structures", Journal of Crystal Growth, Vol. 81 (1987), pp. 552-556.
✓	Clemens, et al., "Growth of BaF ₂ and of BaF ₂ /SrF ₂ layers on (001) oriented GaAs", J. Appl. Phys., Vol. 66, No. 4, 15 Aug. 1989, pp. 1680-1685.
✓	Hung, et al., "Epitaxial growth of alkaline earth fluoride films on HF-treated Si and (NH ₄) ₂ S _x -treated GaAs without <i>in situ</i> cleaning", Appl. Phys. Lett., Vol. 60, No. 2, 13 Jan. 1992, pp. 201-203.

EXAMINER

HUNG K. VU

DATE CONSIDERED

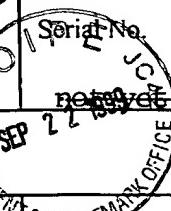
09/21/00

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

Form PTO-1449
(Rev. 2-32)U.S. Department of Commerce
Patent & Trademark Office

Atty. Docket No.

82149

INFORMATION DISCLOSURE STATEMENT
(Use several sheets if necessary)Applicant
Stumborg, et al.

Filing Date 08/20/98

Concurrently

Group
2811

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
V	5,690,737	11/25/95	Santiago et al.	117	92	-
V	5,695,810	12/9/97	Dubin et al.	427	96	-
V	5,824,599	10/20/98	Schacham-Diamond, et al.	437	230	-

FOREIGN PATENT DOCUMENTS

	Document	Date	Country	Class	Sub-class	Translation Yes/No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

V	Chaudhari, et al., "Calcium Fluoride thin films on GaAs (100) for possible metal-insulator-semiconductor applications", Appl. Phys. lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.
V	Colbow, et al., "Photoemission study of the formation of SrF ₂ /GaAs(100) and BaF ₂ /GaAs(100) interfaces", Physical Review B, Vol. 49, No. 3, 15 Jan. 1994, pp. 1750-1756.
V	Chu, et al., "The Role of Barium in the Heteroepitaxial Growth of Insulator and Semiconductors on Silicon", Mat. Res. Symp. Proc., Vol. 334, 1994, pp. 501-506.
V	Stumborg, et al., "Determination of growth mechanisms of MBE grown BaF ₂ on Si(100) by target angle dependence of RBS yields", Nucl. Instr. and Methods in Physics Res. B, Vol. 95, 1995, pp. 319-322.
V	Stumborg, et al., "Growth and interfacial chemistry of insulating (100) barium fluoride on gallium arsenide", J. Appl. Phys., Vol. 77, No. 6, 15 March 1995, pp. 2739-2744.
V	Stumborg, et al., "Surface chemical state populations in the molecular beam epitaxy deposition of BaF ₂ on GaAs by x-ray photoelectron spectroscopy and heavy-ion backscattering spectroscopy", J. Vac. Sci. Technol., Vol. 14, No. 1, Jan./Feb. 1996, pp. 69-79.
V	Chu, et al., "Heteroepitaxial deposition of Group IIa fluorides on gallium arsenide", Mat. Sci. and Eng. B, Vol. B47, 1997, pp. 224-234.

EXAMINER

HUNG K. VU

DATE CONSIDERED

09/21/00

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

Form PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent & Trademark Office	Atty. Docket No.	Serial No.
		NC79329	09/137,084
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant STUMBORG ET AL.	
NOV - 1 1999		Filing Date 8/20/98	Group 2811

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

HUNG K. VU

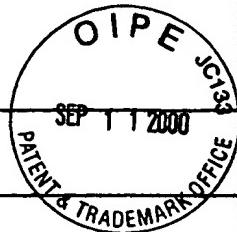
DATE CONSIDERED

09/21/00

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

Form PTO-1449 U.S. Department of Commerce Patent & Trademark Office	Atty. Docket No. N.C. 79329	Serial No. 09/137,084
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		
Applicant Stumborg, et al.		Filing Date August 20, 1998
		Group 2811



U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

		Document	Date	Country	Class	Sub-class	Translation Yes/No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

HUNG K. VU

DATE CONSIDERED

09/21/00

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.